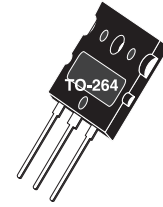


## High Speed PT IGBT


POWER MOS 8® is a high speed Punch-Through switch-mode IGBT. Low  $E_{off}$  is achieved through leading technology silicon design and lifetime control processes. A reduced  $E_{off}$  -  $V_{CE(ON)}$  tradeoff results in superior efficiency compared to other IGBT technologies. Low gate charge and a greatly reduced ratio of  $C_{res}/C_{ies}$  provide excellent noise immunity, short delay times and simple gate drive. The intrinsic chip gate resistance and capacitance of the poly-silicone gate structure help control di/dt during switching, resulting in low EMI, even when switching at high frequency.


**APT80GA90LD40**

Combi (IGBT and Diode)



### FEATURES

- Fast switching with low EMI
- Very Low  $E_{off}$  for maximum efficiency
- Ultra low  $C_{res}$  for improved noise immunity
- Low conduction loss
- Low gate charge
- Increased intrinsic gate resistance for low EMI
- RoHS compliant 

### TYPICAL APPLICATIONS

- ZVS phase shifted and other full bridge
- Half bridge
- High power PFC boost
- Welding
- UPS, solar, and other inverters
- High frequency, high efficiency industrial

### Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
$V_{CES}$	Collector Emitter Voltage	900	V
$I_{C1}$	Continuous Collector Current @ $T_c = 25^\circ\text{C}$	145	A
$I_{C2}$	Continuous Collector Current @ $T_c = 100^\circ\text{C}$	80	
$I_{CM}$	Pulsed Collector Current <sup>1</sup>	239	
$V_{GE}$	Gate-Emitter Voltage <sup>2</sup>	$\pm 30$	V
$P_D$	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	625	W
SSOA	Switching Safe Operating Area @ $T_j = 150^\circ\text{C}$	239A @ 900V	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	°C
$T_L$	Lead Temperature for Soldering: 0.063" from Case for 10 Seconds	300	

### Static Characteristics

 $T_J = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1.0mA$	900			V
$V_{CE(on)}$	Collector-Emitter On Voltage	$V_{GE} = 15V, I_C = 47A$		2.5 2.2	3.1	
		$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$				
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	3	4.5	6	µA
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{CE} = 900V, V_{GE} = 0V$			350 1500	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GS} = \pm 30V$			$\pm 100$	nA

## Dynamic Characteristics

$T_J = 25^\circ\text{C}$  unless otherwise specified

APT80GA90LD40

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1\text{MHz}$		4560		pF
$C_{oes}$	Output Capacitance			411		
$C_{res}$	Reverse Transfer Capacitance			62		
$Q_g^3$	Total Gate Charge	Gate Charge $V_{GE} = 15V$ $V_{CE} = 450V$ $I_C = 47A$		200		nC
$Q_{ge}$	Gate-Emitter Charge			30		
$Q_{gc}$	Gate-Collector Charge			72		
SSOA	Switching Safe Operating Area	$T_J = 150^\circ\text{C}, R_G = 4.7\Omega^4, V_{GE} = 15V,$ $L = 100\mu\text{H}, V_{CE} = 900V$	239			A
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 47A$ $R_G = 4.7\Omega^4$ $T_J = +25^\circ\text{C}$		18		ns
$t_r$	Current Rise Time			29		
$t_{d(off)}$	Turn-Off Delay Time			149		
$t_f$	Current Fall Time			85		
$E_{on2}$	Turn-On Switching Energy			1652		
$E_{off}^6$	Turn-Off Switching Energy		1389		$\mu\text{J}$	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 47A$ $R_G = 4.7\Omega^4$ $T_J = +125^\circ\text{C}$		18		ns
$t_r$	Current Rise Time			31		
$t_{d(off)}$	Turn-Off Delay Time			192		
$t_f$	Current Fall Time			128		
$E_{on2}$	Turn-On Switching Energy			2813		
$E_{off}^6$	Turn-Off Switching Energy		2082		$\mu\text{J}$	

## Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance (IGBT)	-	-	0.2	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Junction to Case Thermal Resistance (Diode)			.61	
$W_T$	Package Weight	-	6.1	-	g
Torque	Mounting Torque (TO-264 Package), 4-40 or M3 screw			10	in-lbf

1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

2 Pulse test: Pulse Width <  $380\mu\text{s}$ , duty cycle < 2%.

3 See Mil-Std-750 Method 3471.

4  $R_G$  is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

5  $E_{on2}$  is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

6  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

**Microsemi reserves the right to change, without notice, the specifications and information contained herein.**

# Typical Performance Curves

APT80GA90LD40

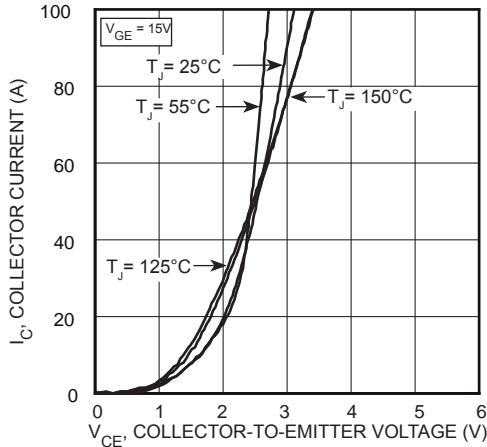


FIGURE 1, Output Characteristics ( $T_J = 25^\circ\text{C}$ )

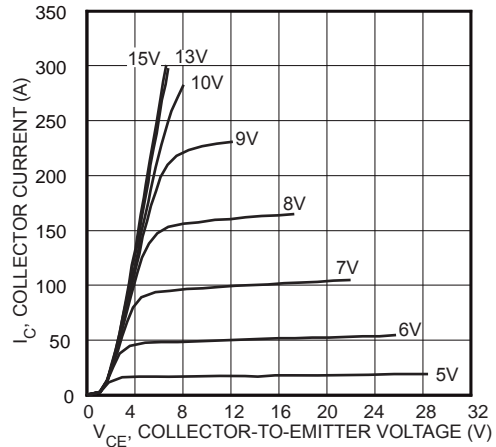


FIGURE 2, Output Characteristics ( $T_J = 25^\circ\text{C}$ )

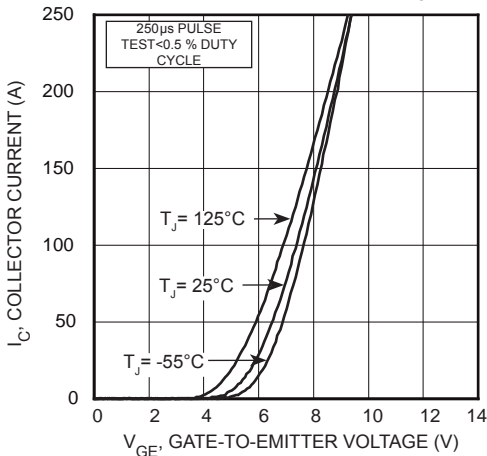


FIGURE 3, Transfer Characteristics

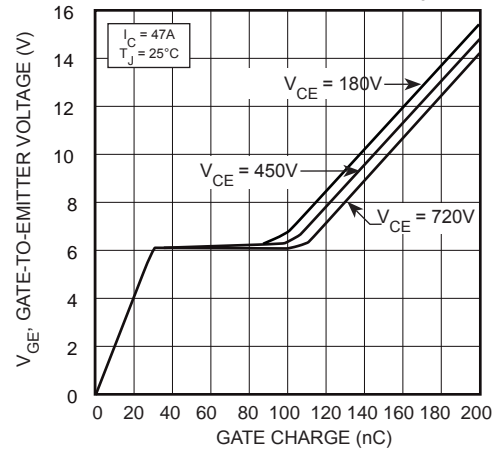


FIGURE 4, Gate charge

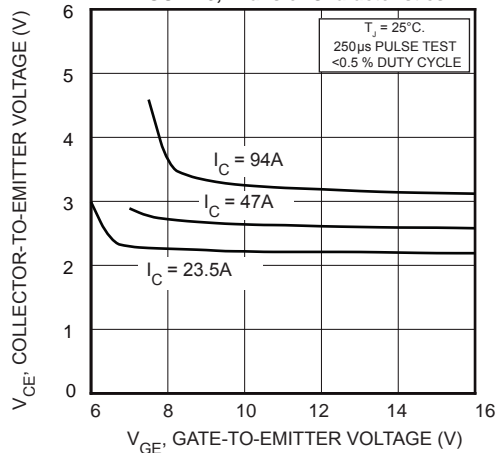


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

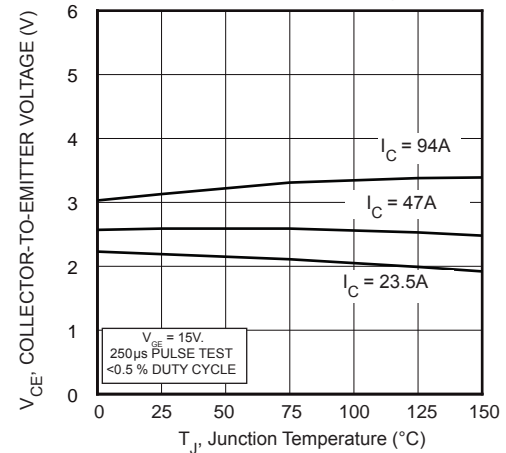


FIGURE 6, On State Voltage vs Junction Temperature

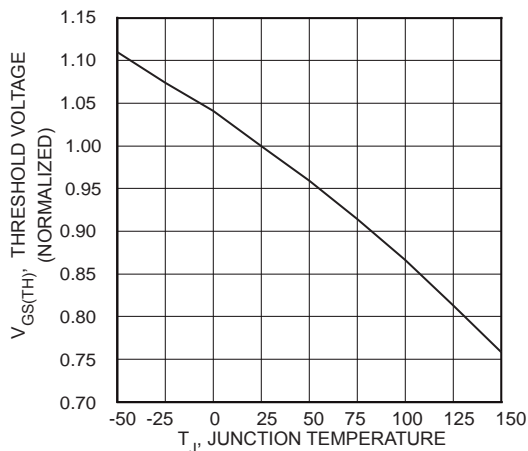


FIGURE 7, Threshold Voltage vs Junction Temperature

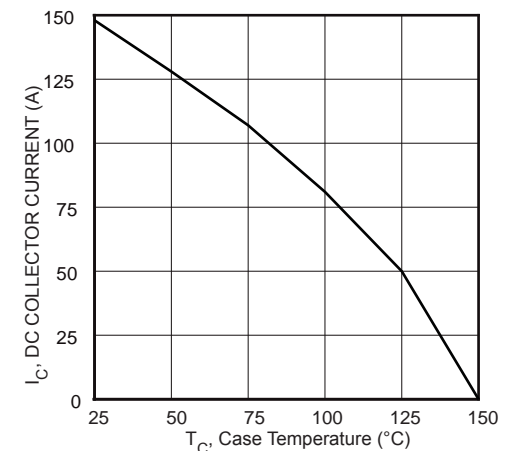


FIGURE 8, DC Collector Current vs Case Temperature

# Typical Performance Curves

APT80GA90LD40

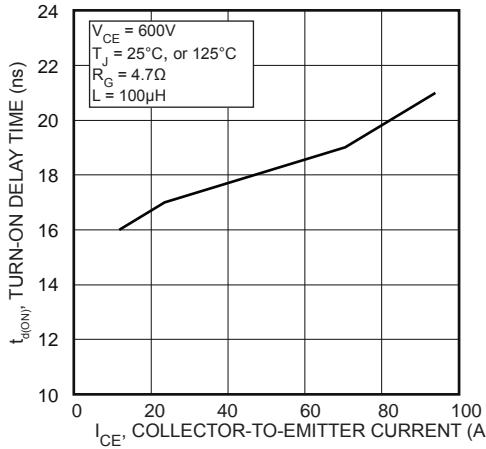


FIGURE 9, Turn-On Delay Time vs Collector Current

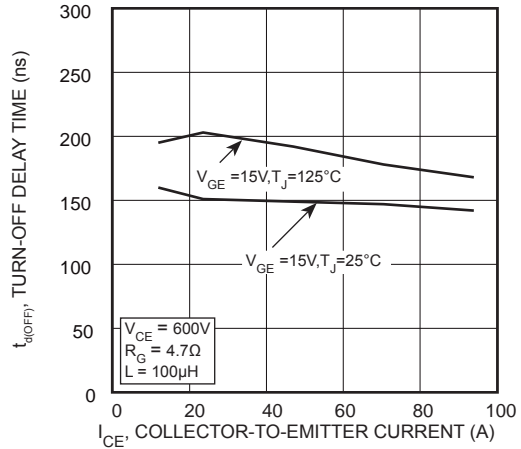


FIGURE 10, Turn-Off Delay Time vs Collector Current

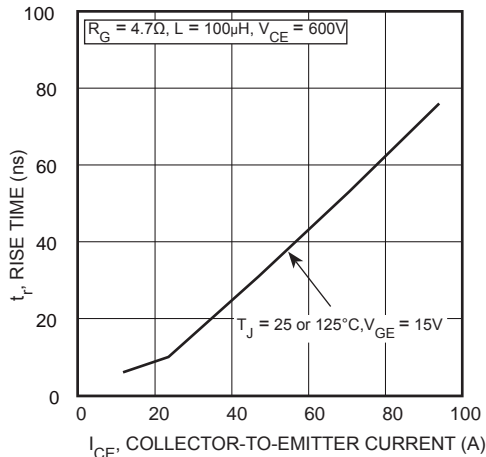


FIGURE 11, Current Rise Time vs Collector Current

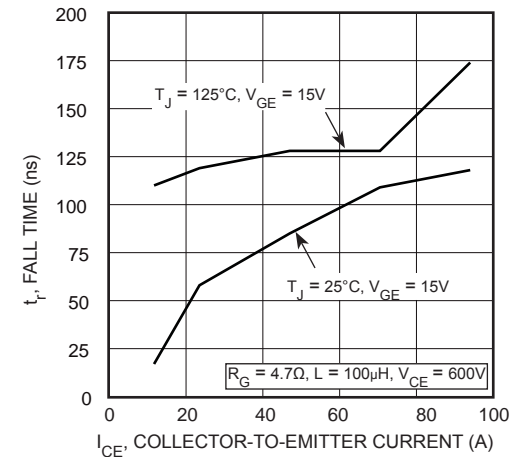


FIGURE 12, Current Fall Time vs Collector Current

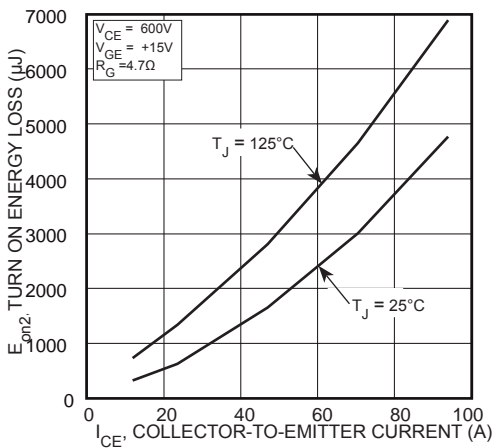


FIGURE 13, Turn-On Energy Loss vs Collector Current

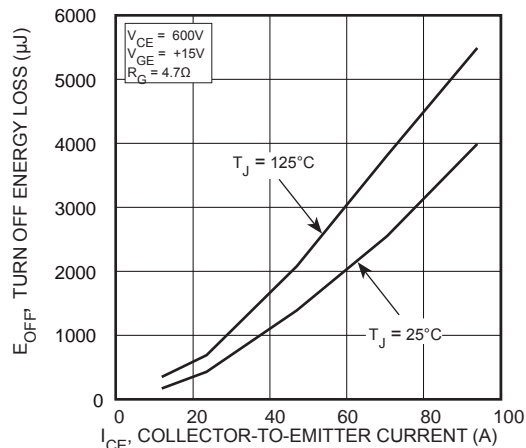


FIGURE 14, Turn-Off Energy Loss vs Collector Current

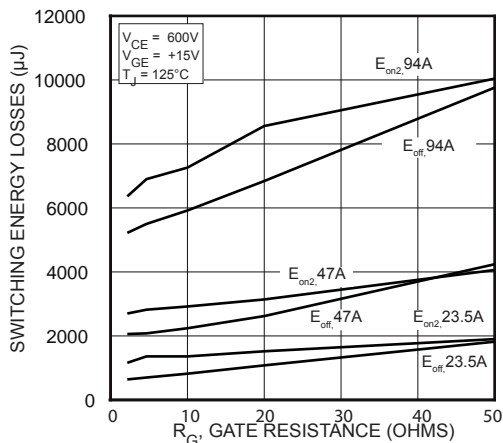


FIGURE 15, Switching Energy Losses vs Gate Resistance

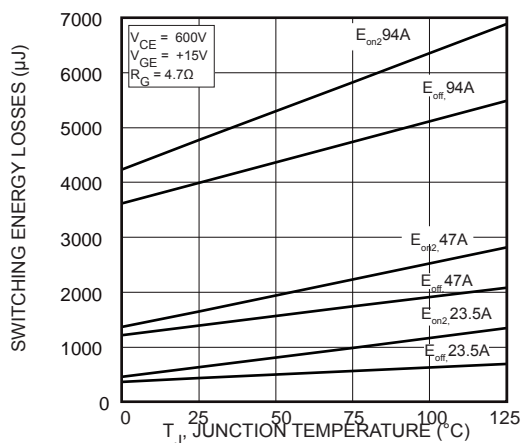


FIGURE 16, Switching Energy Losses vs Junction Temperature

# Typical Performance Curves

APT80GA90LD40

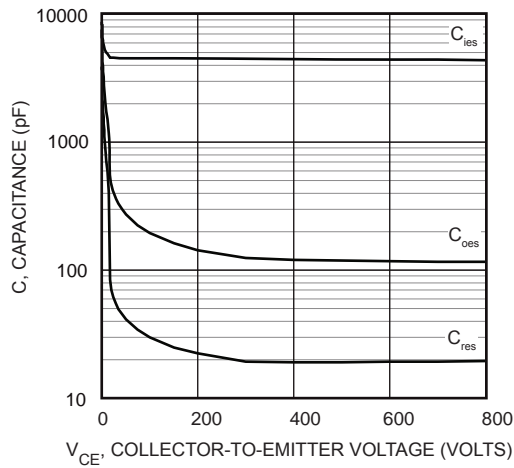


FIGURE 17, Capacitance vs Collector-To-Emitter Voltage

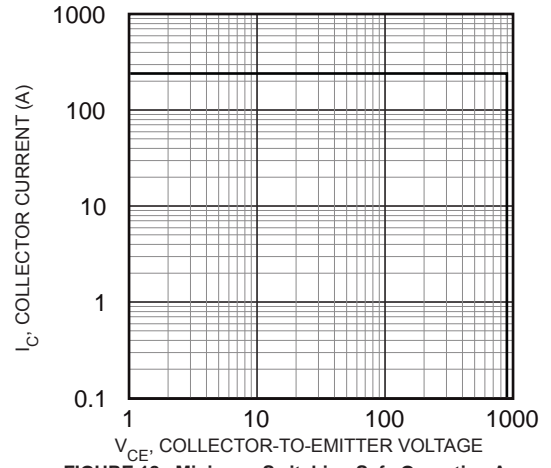


FIGURE 18, Minimum Switching Safe Operating Area

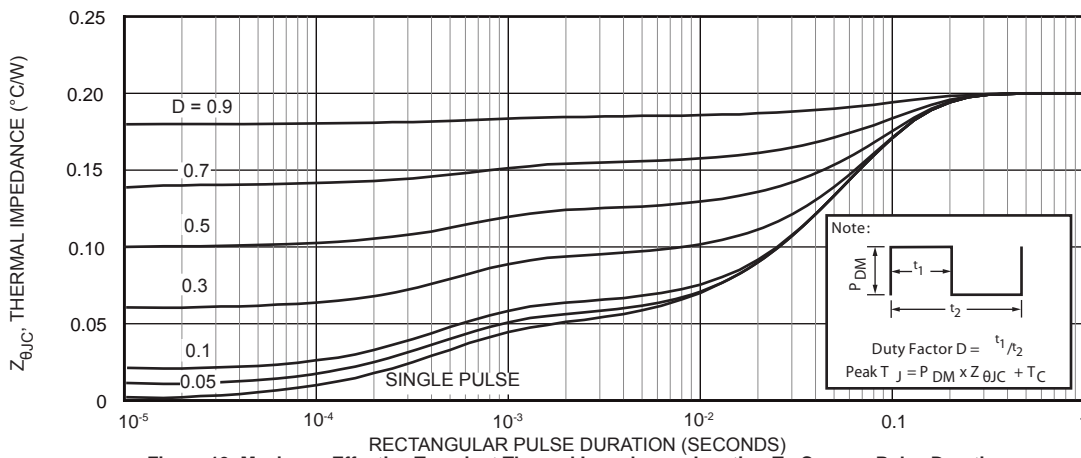


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

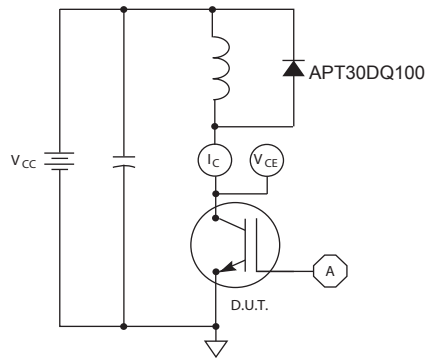


Figure 20 Inductive Switching Test Circuit

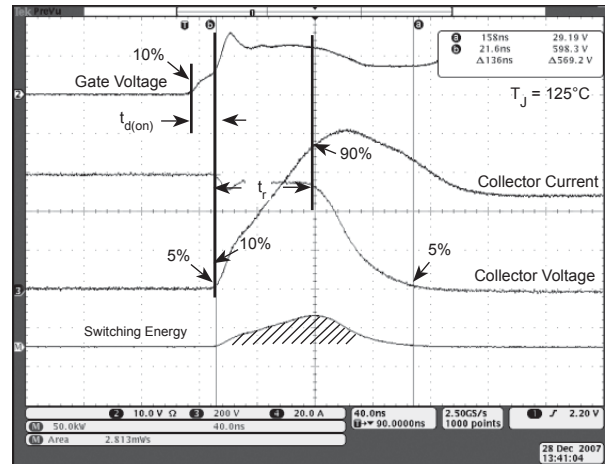


Figure 21, Turn-on Switching Waveforms and Definitions

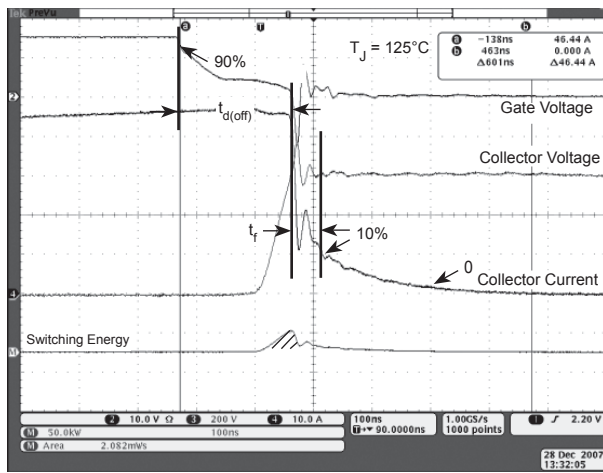


Figure 22, Turn-off Switching Waveforms and Definitions

# ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

## MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

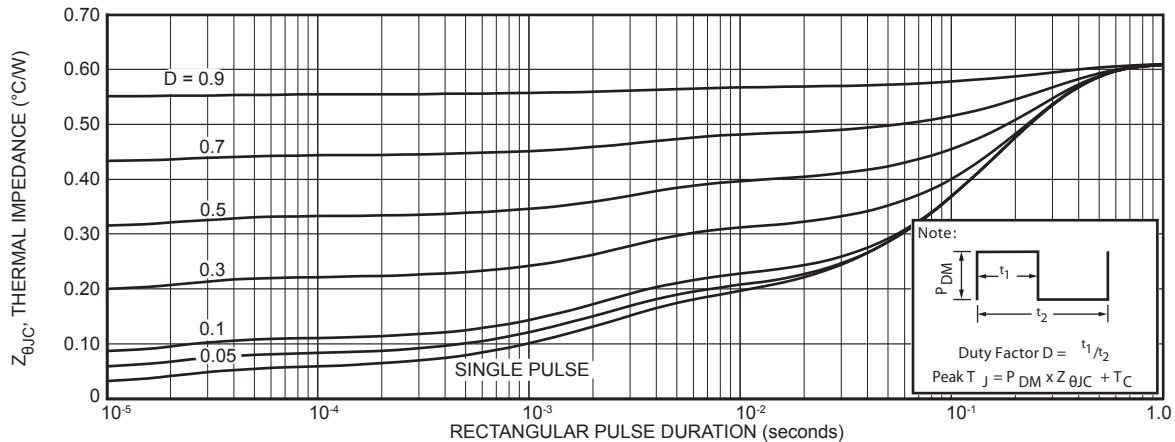
Symbol	Characteristic / Test Conditions	APT80GA90LD40	Unit
$I_{F(AV)}$	Maximum Average Forward Current ( $T_C = 106^\circ\text{C}$ , Duty Cycle = 0.5)	40	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	60	
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3 ms)	210	

## STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Type	Max	Unit
$V_F$	Forward Voltage		$I_F = 40\text{A}$	2.5	Volts
			$I_F = 80\text{A}$	3.08	
			$I_F = 40\text{A}, T_J = 125^\circ\text{C}$	1.97	

## DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	25	-	ns	
$t_{rr}$	Reverse Recovery Time	$I_F = 40\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 25^\circ\text{C}$	-	250	-	ns	
$Q_{rr}$	Reverse Recovery Charge		-	415	-		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	4	-		Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 40\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 125^\circ\text{C}$	-	315	-	ns	
$Q_{rr}$	Reverse Recovery Charge		-	1650	-		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	9	-		Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 40\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 125^\circ\text{C}$	-	145	-	ns	
$Q_{rr}$	Reverse Recovery Charge		-	2660	-		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	29	-		Amps



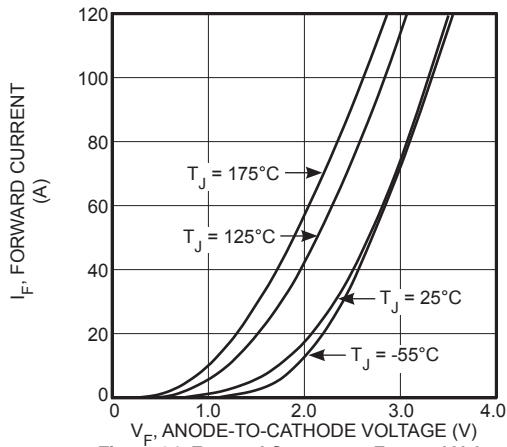


Figure 24. Forward Current vs. Forward Voltage

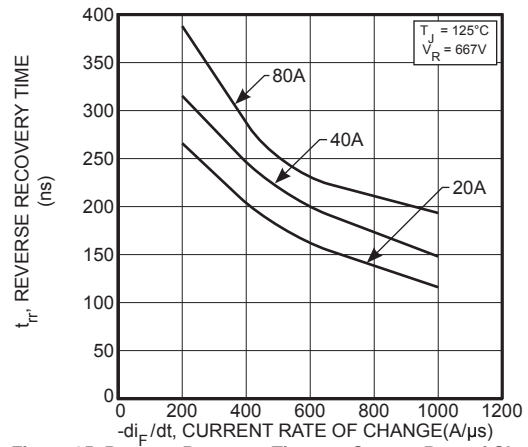


Figure 25. Reverse Recovery Time vs. Current Rate of Change

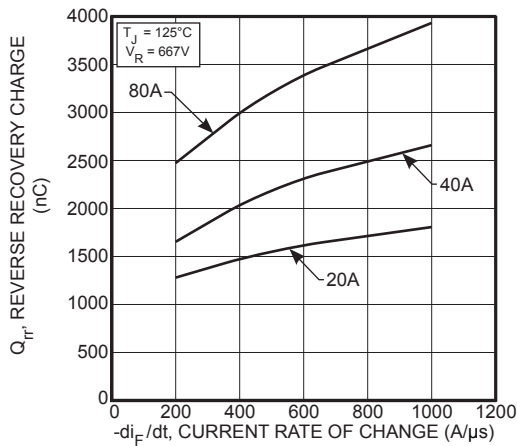


Figure 26. Reverse Recovery Charge vs. Current Rate of Change

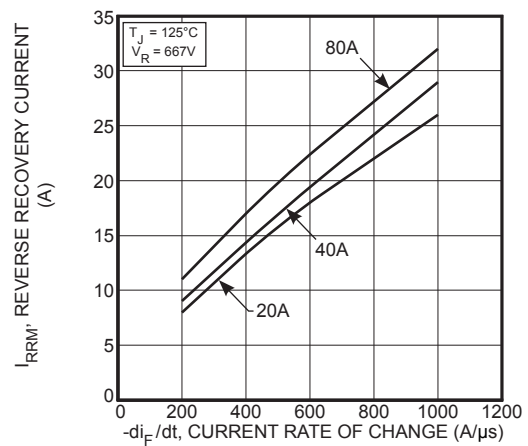


Figure 27. Reverse Recovery Current vs. Current Rate of Change

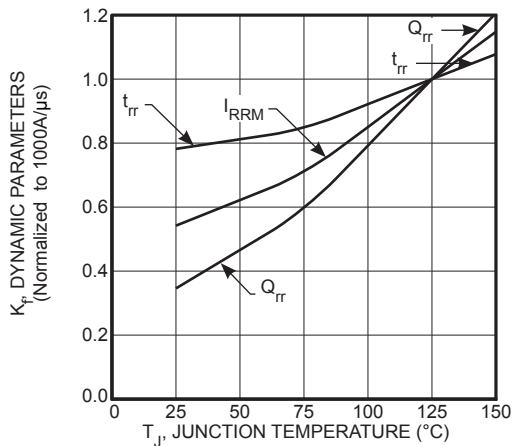


Figure 28. Dynamic Parameters vs. Junction Temperature

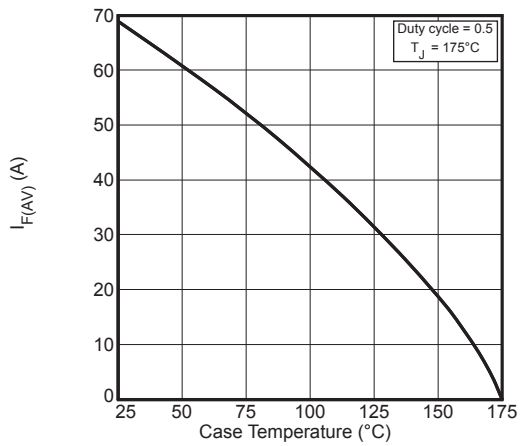


Figure 29. Maximum Average Forward Current vs. Case Temperature

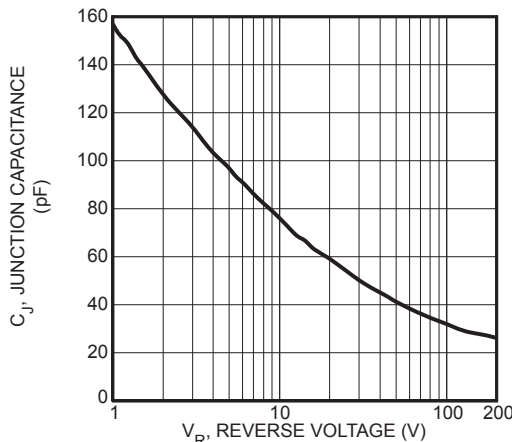


Figure 30. Junction Capacitance vs. Reverse Voltage



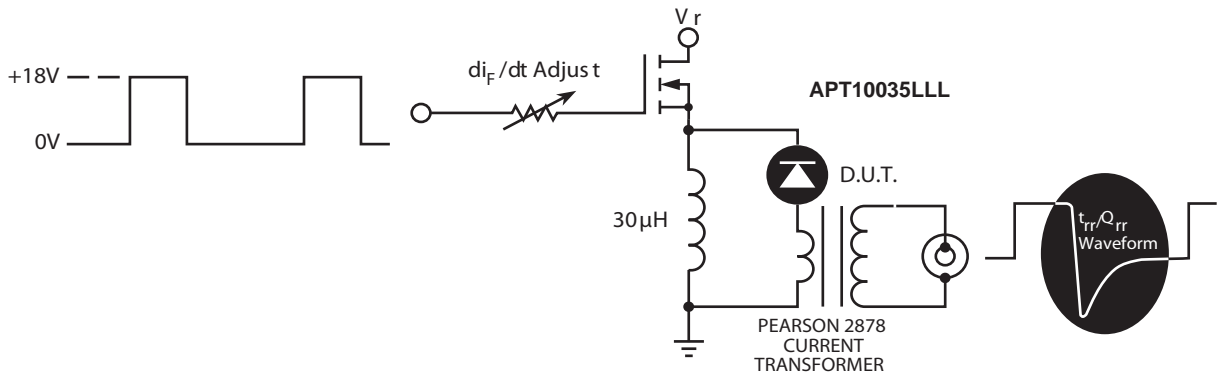


Figure 31. Diode Test Circuit

- 1 I<sub>F</sub> - Forward Conduction Current
- 2 di<sub>F</sub>/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I<sub>R<sub>RRM</sub></sub> - Maximum Reverse Recovery Current
- 4 t<sub>rr</sub> - Reverse Recovery Time measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I<sub>R<sub>RRM</sub></sub> and 0.25 I<sub>R<sub>RRM</sub></sub> passes through zero.
- 5 Q<sub>rr</sub> - Area Under the Curve Defined by I<sub>R<sub>RRM</sub></sub> and t<sub>rr</sub>.

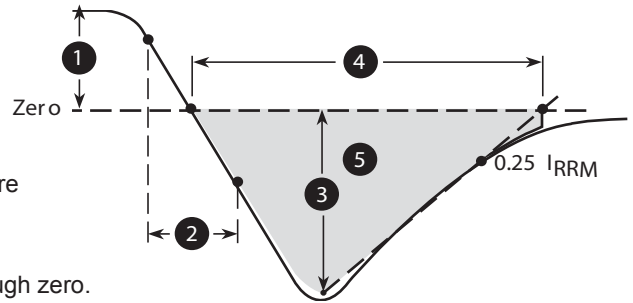
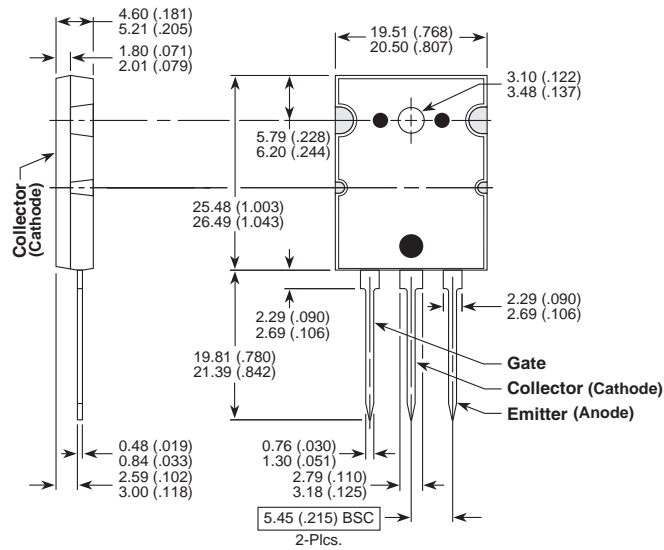


Figure 32. Diode Reverse Recovery Waveform Definition

TO-264 (L) Package Outline





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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